

TLP550

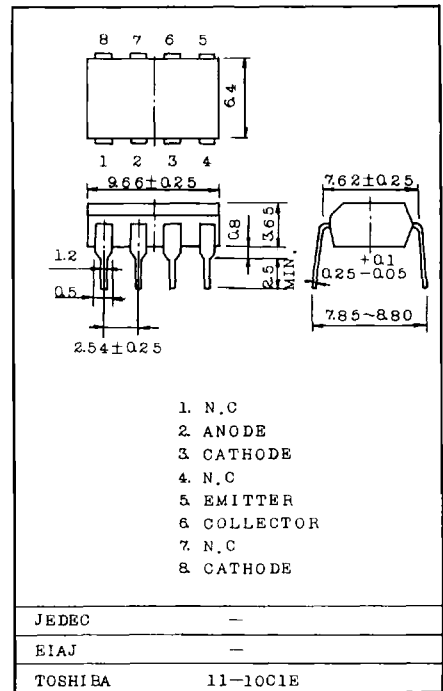
GaAs IRED & PHOTO-IC

DIGITAL LOGIC ISOLATION.
 LINE RECEIVER FEEDBACK CONTROL.
 POWER SUPPLY CONTROL.
 SWITCHING POWER SUPPLY.
 TRANSISTOR INVERTOR.

TLP550 constructs a high emitting diode and a
 one chip photo diode-transistor.
 TLP550 has no base connection, and is suitable
 for application at noisy environmental condi-
 tion.

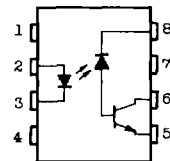
This unit is 8-lead DIP package.

- . Isolation Voltage : 2500Vrms Min.
- . Switching Speed : $t_{pHL}, t_{pLH}=0.5\mu s$ (Typ.)
($R_L=1.9k\Omega$)
- . TTL Compatible
- . UL Recognized : File No. E67349

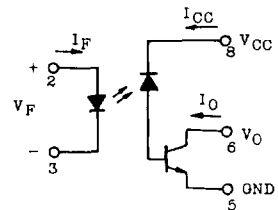


1. N.C
2. ANODE
3. CATHODE
4. N.C
5. EMITTER
6. COLLECTOR
7. N.C
8. CATHODE

PIN CONFIGURATIONS (TOP VIEW)



SCHEMATIC



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current (Note 1)	I _F	25	mA
	Pulse Forward Current (Note 2)	I _{FP}	50	
	Peak Transient Forward Current (Note 3)	I _{FPT}	1	A
	Reverse Voltage	V _R	5	V
	Diode Power Dissipation (Note 4)	P _D	45	mW
DETECTOR	Output Current	I _O	8	mA
	Peak Output Current	I _{OP}	16	
	Supply Voltage	V _{CC}	-0.5 ~ 15	V
	Output Voltage	V _O	-0.5 ~ 15	
	Output Power Dissipation (Note 5)	P _O	100	mW
Operating Temperature Range		T _{opr}	-55 ~ 100	°C
Storage Temperature Range		T _{stg}	-55 ~ 125	°C
Lead Solder Temperature (10 sec.)		T _{sold}	260	°C
Isolation Voltage (AC, 1 min., R.H=40 ~ 60%, Note 6)		BV _S	2500	V _{rms}

Note 1 : Derate 0.8mA above 70°C.

Note 2 : 50% duty cycle, 1ms pulse width.
Derate 1.6mA/°C above 70°C.

Note 3 : Pulse width 1μs, 300pps.

Note 4 : Derate 0.9mW/°C above 70°C.

Note 5 : Derate 2mW/°C above 70°C.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

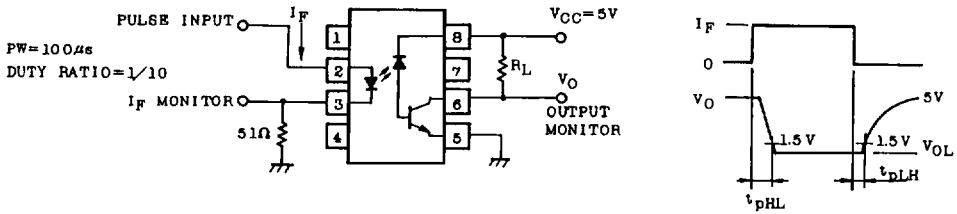
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
LED	Forward Voltage	V _F	I _F =16mA	1.45	1.65	1.85	V	
	Forward Voltage Temperature Coefficient	ΔV _F /ΔTa	I _F =16mA	-	-2	-	mV/°C	
	Reverse Current	I _R	V _R =5V	-	-	10	μA	
	Capacitance Between Terminals	C _T	V _F =0, f=1MHz	-	60	-	pF	
DETECTOR	High Level Output Current	I _{OH} (1)	I _F =0mA, V _{CC} =V _O =5.5V	-	3	500	nA	
		I _{OH} (2)	I _F =0mA, V _{CC} =V _O =15V	-	-	5	μA	
		I _{OH}	I _F =0mA, V _{CC} =V _O =15V, Ta=70°C	-	-	50	μA	
High Level Supply Voltage	I _{CCH}	I _F =0mA, V _{CC} =15V	-	0.01	1	μA		
COUPLED	Current Transfer Ratio	I _O /I _F	I _F =16mA V _{CC} =4.5V V _O =0.4V	Ta=25°C	10	30	-	%
				rank:0	19	30	-	
				Ta=0~70°C	5	-	-	
				rank:0	15	-	-	
Low Level Output Voltage	V _{OL}	I _F =16mA, V _{CC} =4.5V I _O =1.1mA (rank 0: I _O =2.4mA)	-	-	0.4	V		
Isolation Resistance	R _S	R.H.=40~60%, V=1kV DC (Note 6)	-	1012	-	Ω		
Stray Capacitance Between Input to Output	C _S	V=0, f=1MHz	-	0.8	-	pF		

SWITCHING CHARACTERISTICS (Ta=25°C)

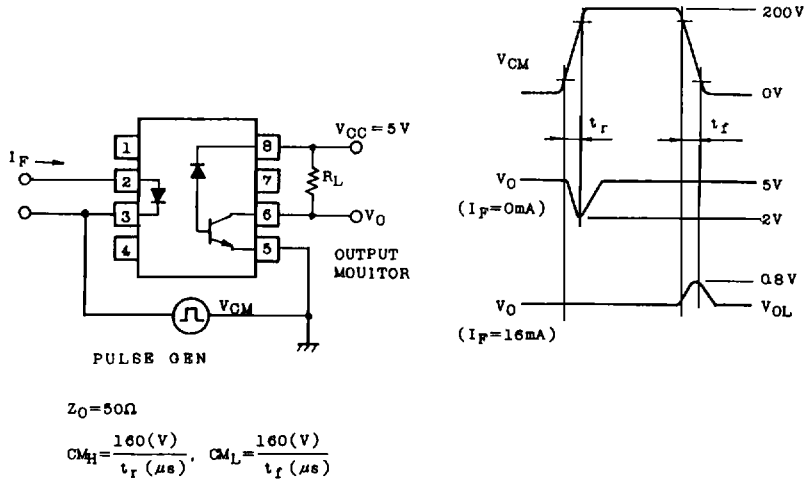
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Propagation Delay Time (H → L)	t _{pHL}	I _F =0 → 16mA, V _{CC} =5V, R _L =4.1kΩ (Note 7)	rank 0: R _L =1.9kΩ	-	0.3	0.8	μs
			rank 0: R _L =1.9kΩ	-	0.5	0.8	
Propagation Delay Time (L → H)	t _{pLH}	I _F =16 → 0mA, V _{CC} =5V, R _L =4.1kΩ (Note 7)	rank 0: R _L =1.9kΩ	-	1.0	2.0	
			rank 0: R _L =1.9kΩ	-	0.6	1.2	
Common Mode Transient Immunity at High Output Level	C _{MH}	I _F =0mA, V _{CM} =200Vp-p R _L =4.1kΩ (rank 0: R _L =1.9kΩ) (Note 8)	-	1500	-	V/μs	
Common Mode Transient Immunity at Low Output Level	C _{ML}	I _F =16mA, V _{CM} =200Vp-p R _L =4.1kΩ (rank 0: R _L =1.9kΩ) (Note 8)	-	-1500	-		

Note 6. Device considered a two-terminal device : Pins 1, 2, 3 and 4 shorted together and Pin 5, 6, 7 and 8 shorted together.

Note 7. Switching time test circuit.



Note 8. Common mode transient immunity test circuit.



Note 9. Maximum electrostatic discharge voltage for any pins: 100V(C=200pF, R=0)

PRECAUTION

Please be careful of the followings.

1. Soldering temperature: 260°C MAX. Soldering time: 10 sec MAX.
(Soldering portion of lead: up to 2mm from the body of the device)
2. Avoid using the Solvents except for the follows, when washing off flux and wiping off stain on the device.
Washing time: 30 sec MAX. Solvents temperature: 45°C MAX.

